

RMLV0408E Series

4Mb Advanced LPSRAM (512-kword × 8-bit)

R10DS0206EJ0300

Rev.3.00

2021.8.18

Description

The RMLV0408E Series is a family of 4-Mbit static RAMs organized 524,288-word × 8-bit, fabricated by Renesas's high-performance Advanced LPSRAM technologies. The RMLV0408E Series has realized higher density, higher performance and low power consumption. The RMLV0408E Series offers low power standby power dissipation; therefore, it is suitable for battery backup systems. It is offered in 32-pin SOP, 32-pin TSOP (II) or 32-pin sTSOP.

Features

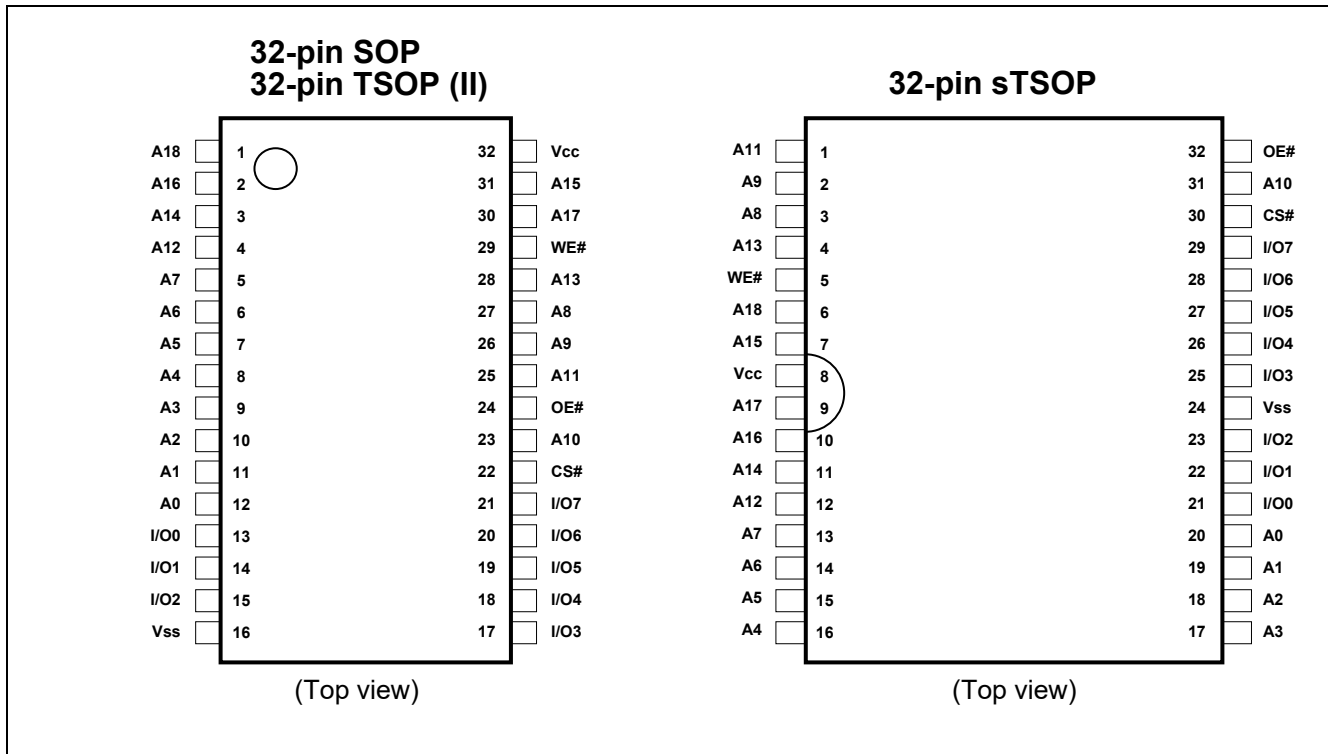
- Single 3V supply: 2.7V to 3.6V
- Access time: 45ns (max.)
- Current consumption:
 - Standby: 0.3μA (typ.)
- Equal access and cycle times
- Common data input and output
 - Three state output
- Directly TTL compatible
 - All inputs and outputs
- Battery backup operation

Orderable part number information

Orderable part number	Access time	Temperature range	Package	Shipping container
RMLV0408EGSA-4S2#AA*	45 ns	-40 ~ +85°C	8mm×13.4mm 32-pin plastic sTSOP	Tray
RMLV0408EGSA-4S2#KA*				Embossed tape
RMLV0408EGSB-4S2#AA*			400-mil 32pin plastic TSOP (II)	Tray
RMLV0408EGSB-4S2#HA*				Embossed tape
RMLV0408EGSP-4S2#CA*			525-mil 32-pin plastic SOP	Tube
RMLV0408EGSP-4S2#HA*				Embossed tape

Note 1. * = Revision code for Assembly site change, etc. (* = 0, 1, etc.)

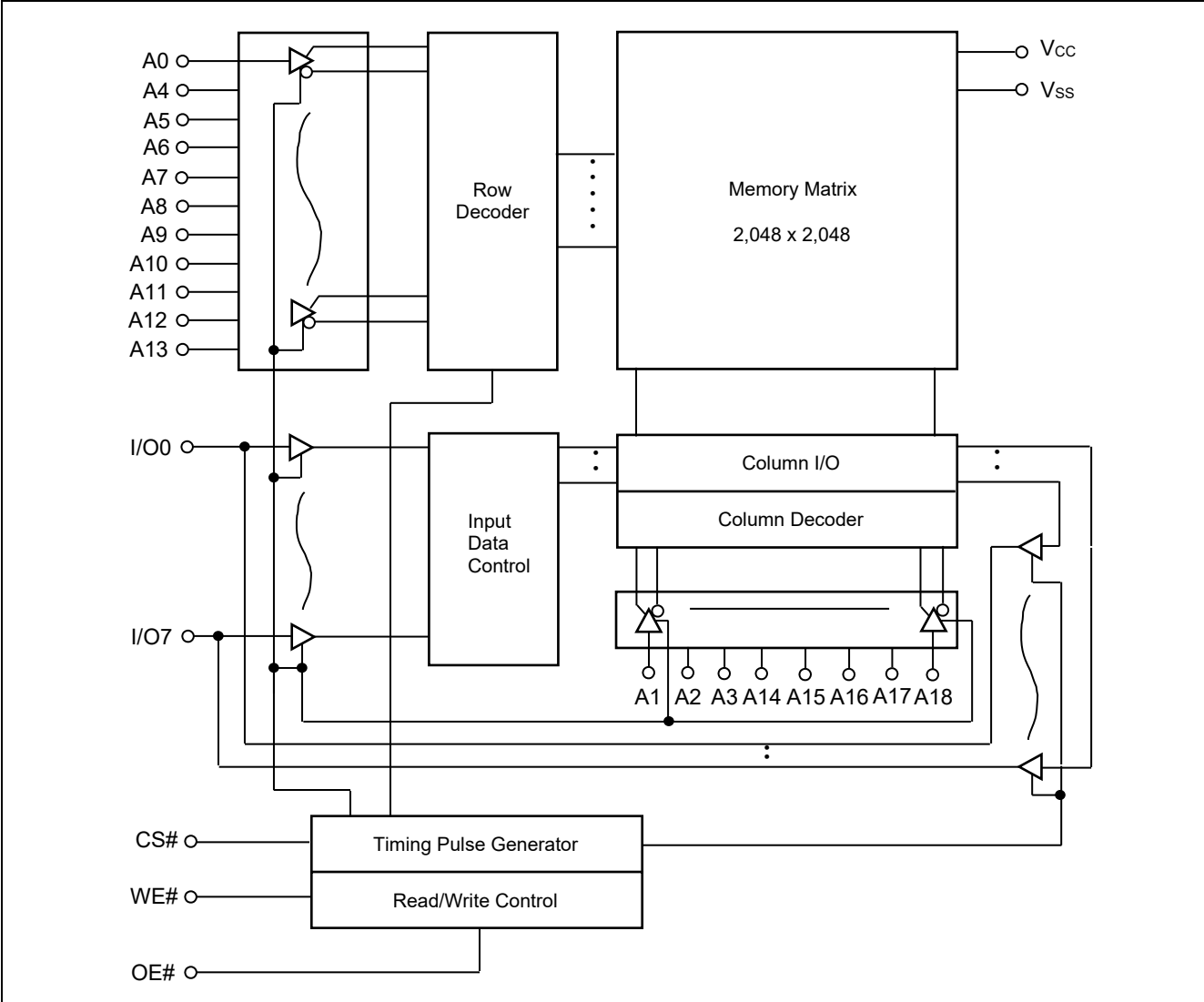
Pin Arrangement



Pin Description

Pin name	Function
Vcc	Power supply
Vss	Ground
A0 to A18	Address input
I/O0 to I/O7	Data input/output
CS#	Chip select
WE#	Write enable
OE#	Output enable

Block Diagram



Operation Table

CS#	WE#	OE#	I/O0 to I/O7	Operation
H	X	X	High-Z	Standby
L	H	L	Dout	Read
L	L	X	Din	Write
L	H	H	High-Z	Output disable

Note 2. H: V_{IH} L: V_{IL} X: V_{IH} or V_{IL}

Absolute Maximum Ratings

Parameter	Symbol	Value	unit
Power supply voltage relative to V_{SS}	V_{CC}	-0.5 to +4.6	V
Terminal voltage on any pin relative to V_{SS}	V_T	-0.5 ³ to $V_{CC}+0.3$ ⁴	V
Power dissipation	P_T	0.7	W
Operation temperature	T_{opr}	-40 to +85	°C
Storage temperature range	T_{stg}	-65 to +150	°C
Storage temperature range under bias	T_{bias}	-40 to +85	°C

Note 3. -3.0V for pulse ≤ 30 ns (full width at half maximum)

4. Maximum voltage is +4.6V.

DC Operating Conditions

Parameter	Symbol	Min.	Typ.	Max.	Unit	Note
Supply voltage	V _{CC}	2.7	3.0	3.6	V	
	V _{SS}	0	0	0	V	
Input high voltage	V _{IH}	2.2	—	V _{CC} +0.3	V	
Input low voltage	V _{IL}	-0.3	—	0.6	V	5
Ambient temperature range	T _a	-40	—	+85	°C	

Note 5. -3.0V for pulse ≤ 30ns (full width at half maximum)

DC Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions	
Input leakage current	I _{LI}	—	—	1	μA	V _{in} = V _{SS} to V _{CC}	
Output leakage current	I _{LO}	—	—	1	μA	CS# = V _{IH} or OE# =V _{IH} or WE#= V _{IL} , V _{I/O} = V _{SS} to V _{CC}	
Operating current	I _{CC}	—	—	10	mA	CS# =V _{IL} , Others = V _{IH} /V _{IL} , I _{I/O} = 0mA	
Average operating current	I _{CC1}	—	—	20	mA	Cycle = 55ns, duty = 100%, I _{I/O} = 0mA, CS# = V _{IL} , Others = V _{IH} /V _{IL}	
		—	—	25	mA	Cycle = 45ns, duty = 100%, I _{I/O} = 0mA, CS# = V _{IL} , Others = V _{IH} /V _{IL}	
	I _{CC2}	—	—	2.5	mA	Cycle = 1μs, duty = 100%, I _{I/O} = 0mA, CS# ≤ 0.2V, V _{IH} ≥ V _{CC} -0.2V, V _{IL} ≤ 0.2V	
Standby current	I _{SB}	—	0.1* ⁶	0.3	mA	CS# =V _{IH} , Others = V _{SS} to V _{CC}	
Standby current	I _{SB1}	—	0.3* ⁶	2	μA	~+25°C	V _{in} = V _{SS} to V _{CC} , CS# ≥ V _{CC} -0.2V
		—	—	3	μA	~+40°C	
		—	—	5	μA	~+70°C	
		—	—	7	μA	~+85°C	
Output high voltage	V _{OH}	2.4	—	—	V	I _{OH} = -1mA	
	V _{OH2}	V _{CC} -0.2	—	—	V	I _{OH} = -0.1mA	
Output low voltage	V _{OL}	—	—	0.4	V	I _{OL} = 2.1mA	
	V _{OL2}	—	—	0.2	V	I _{OL} = 0.1mA	

Note 6. Typical parameter indicates the value for the center of distribution at 3.0V (T_a=25°C), and not 100% tested.

Capacitance

(V_{CC} = 2.7V ~ 3.6V, f = 1MHz, T_a = -40 ~ +85°C)

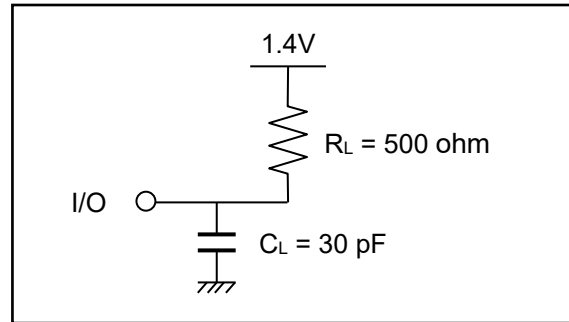
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions	Note
Input capacitance	C _{in}	—	—	8	pF	V _{in} = 0V	7
Input / output capacitance	C _{I/O}	—	—	10	pF	V _{I/O} = 0V	7

Note 7. This parameter is sampled and not 100% tested.

AC Characteristics

Test Conditions ($V_{CC} = 2.7V \sim 3.6V$, $T_a = -40 \sim +85^{\circ}C$)

- Input pulse levels: $V_{IL} = 0.4V$, $V_{IH} = 2.4V$
- Input rise and fall time: 5ns
- Input and output timing reference level: 1.4V
- Output load: See figures (Including scope and jig)



Read Cycle

Parameter	Symbol	Min.	Max.	Unit	Note
Read cycle time	t_{RC}	45	—	ns	
Address access time	t_{AA}	—	45	ns	
Chip select access time	t_{ACS}	—	45	ns	
Output enable to output valid	t_{OE}	—	22	ns	
Output hold from address change	t_{OH}	10	—	ns	
Chip select to output in low-Z	t_{CLZ}	10	—	ns	8,9
Output enable to output in low-Z	t_{OLZ}	5	—	ns	8,9
Chip deselect to output in high-Z	t_{CHZ}	0	18	ns	8,9,10
Output disable to output in high-Z	t_{OHZ}	0	18	ns	8,9,10

Write Cycle

Parameter	Symbol	Min.	Max.	Unit	Note
Write cycle time	t_{WC}	45	—	ns	
Address valid to write end	t_{AW}	35	—	ns	
Chip select to write end	t_{CW}	35	—	ns	
Write pulse width	t_{WP}	35	—	ns	11
Address setup time to write start	t_{AS}	0	—	ns	
Write recovery time from write end	t_{WR}	0	—	ns	
Data to write time overlap	t_{DW}	25	—	ns	
Data hold from write end	t_{DH}	0	—	ns	
Output enable from write end	t_{OW}	5	—	ns	8
Output disable to output in high-Z	t_{OHZ}	0	18	ns	8,10
Write to output in high-Z	t_{WHZ}	0	18	ns	8,10

Note 8. This parameter is sampled and not 100% tested.

9. At any given temperature and voltage condition, t_{CHZ} max is less than t_{CLZ} min, and t_{OHZ} max is less than t_{OLZ} min, for any device.

10. t_{CHZ} , t_{OHZ} and t_{WHZ} are defined as the time when the I/O pins enter a high-impedance state and are not referred to the I/O levels.

11. t_{WP} is the interval between write start and write end.

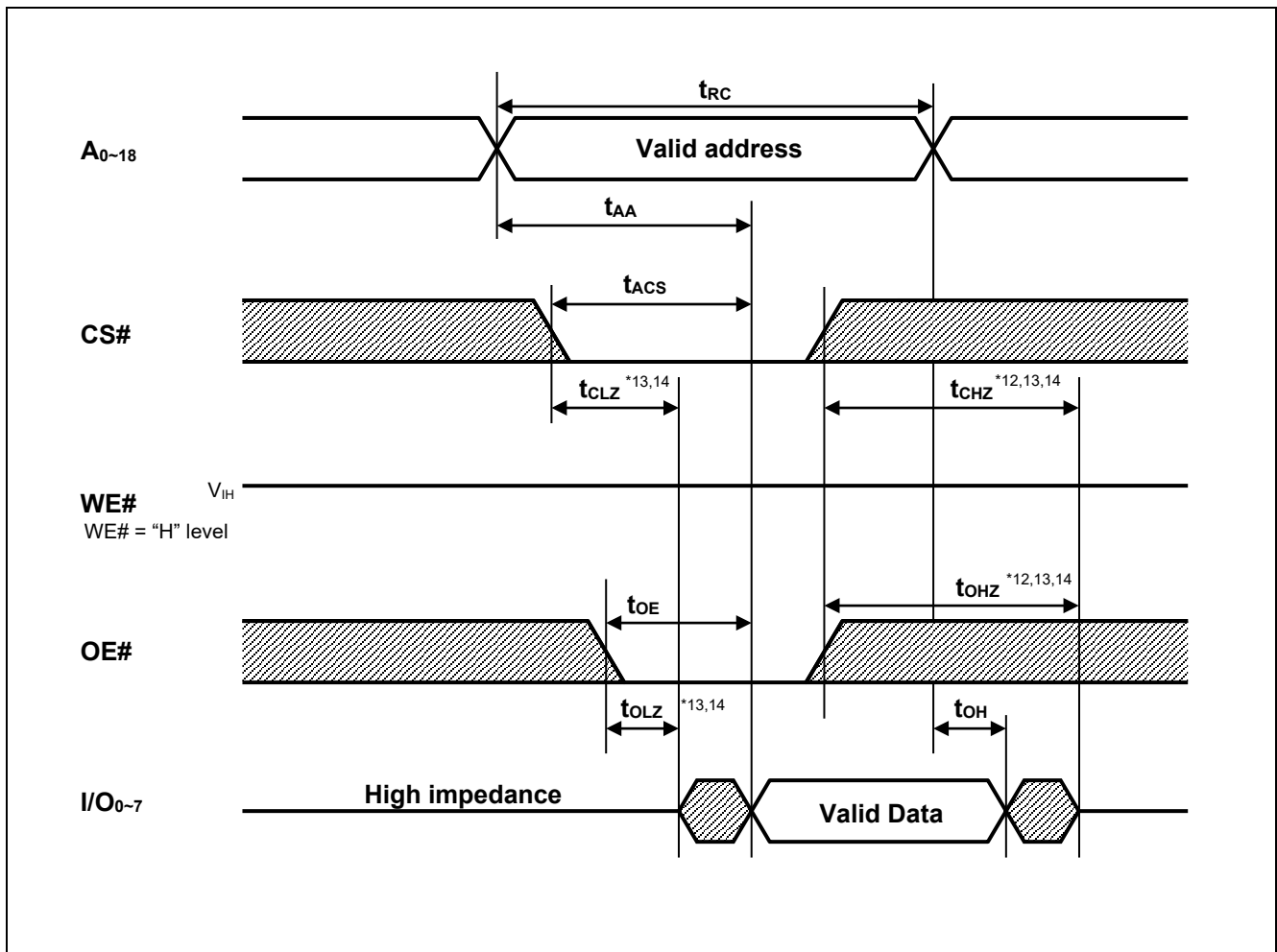
A write starts when both of CS# and WE# become active

A write is performed during the overlap of a low CS#, a low WE#

A write ends when any of CS#, WE# becomes inactive.

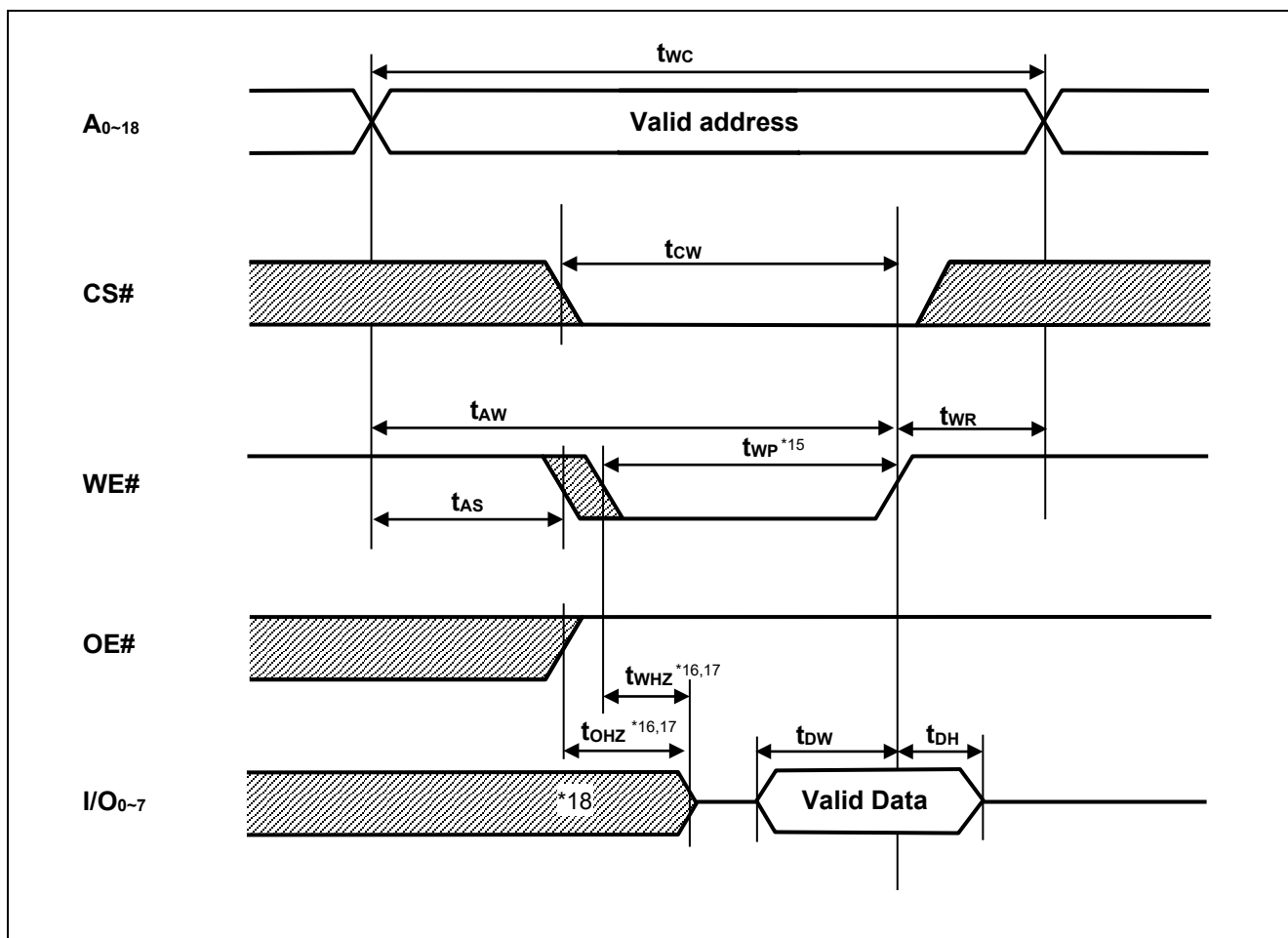
Timing Waveforms

Read Cycle



- Note 12. t_{CHZ} and t_{OHZ} are defined as the time when the I/O pins enter a high-impedance state and are not referred to the I/O levels.
13. This parameter is sampled and not 100% tested.
14. At any given temperature and voltage condition, t_{CHZ} max is less than t_{CLZ} min, and t_{OHZ} max is less than t_{OLZ} min, for any device.

Write Cycle (1) (WE# CLOCK, OE#="H" while writing)



Note 15. t_{wp} is the interval between write start and write end.

A write starts when both of CS# and WE# become active.

A write is performed during the overlap of a low CS# and a low WE#.

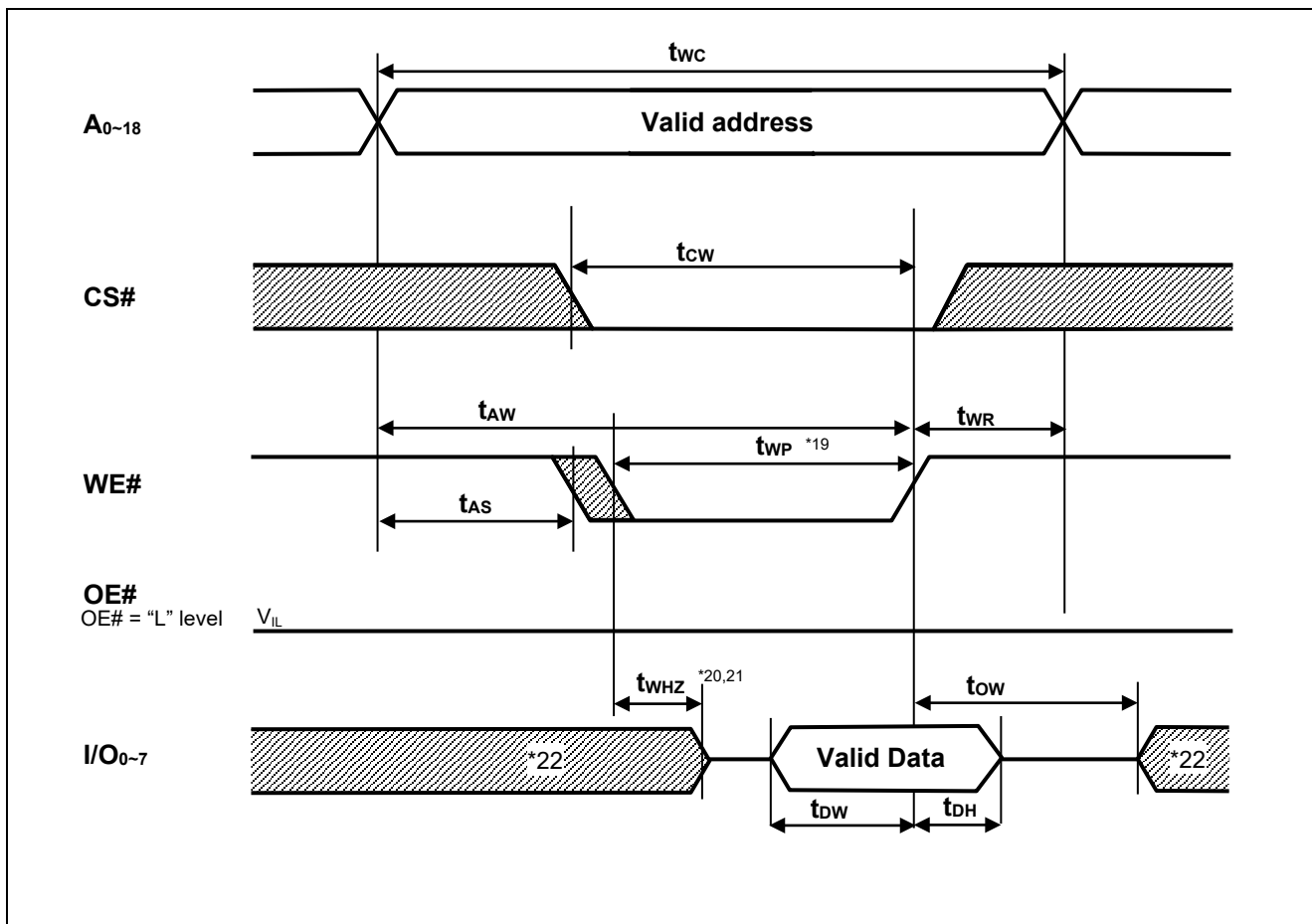
A write ends when any of CS# or WE# becomes inactive.

16. t_{ohz} and t_{whz} are defined as the time when the I/O pins enter a high-impedance state and are not referred to the I/O levels.

17. This parameter is sampled and not 100% tested.

18. During this period, I/O pins are in the output state so input signals must not be applied to the I/O pins.

Write Cycle (2) (WE# CLOCK, OE# Low Fixed)



Note 19. t_{wp} is the interval between write start and write end.

A write starts when both of CS# and WE# become active.

A write is performed during the overlap of a low CS# and a low WE#.

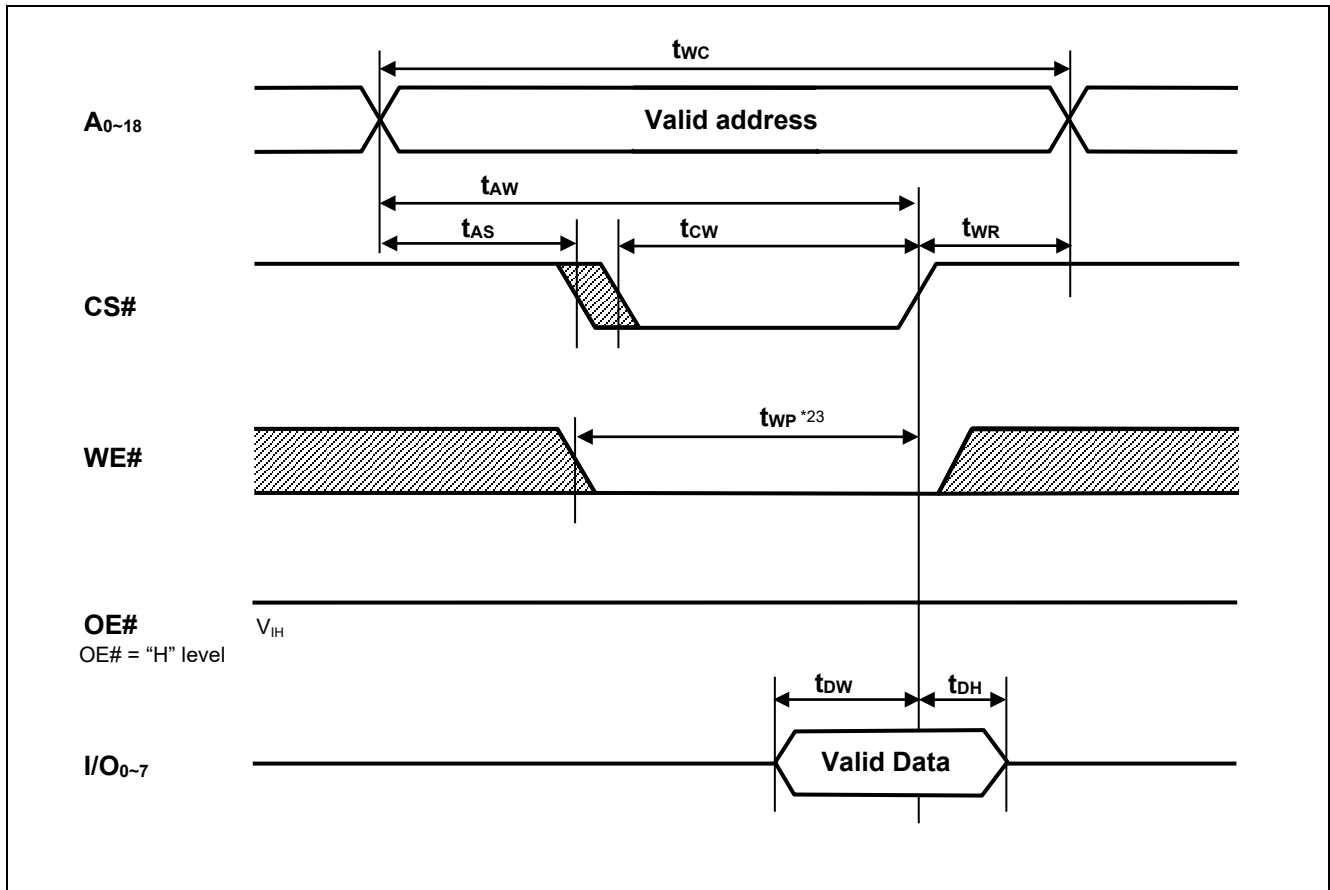
A write ends when any of CS# or WE# becomes inactive.

20. t_{whz} is defined as the time when the I/O pins enter a high-impedance state and are not referred to the I/O levels.

21. This parameter is sampled and not 100% tested.

22. During this period, I/O pins are in the output state so input signals must not be applied to the I/O pins.

Write Cycle (3) (CS# CLOCK)



Note 23. t_{WP} is the interval between write start and write end.

A write starts when both of CS# and WE# become active.

A write is performed during the overlap of a low CS# and a low WE#.

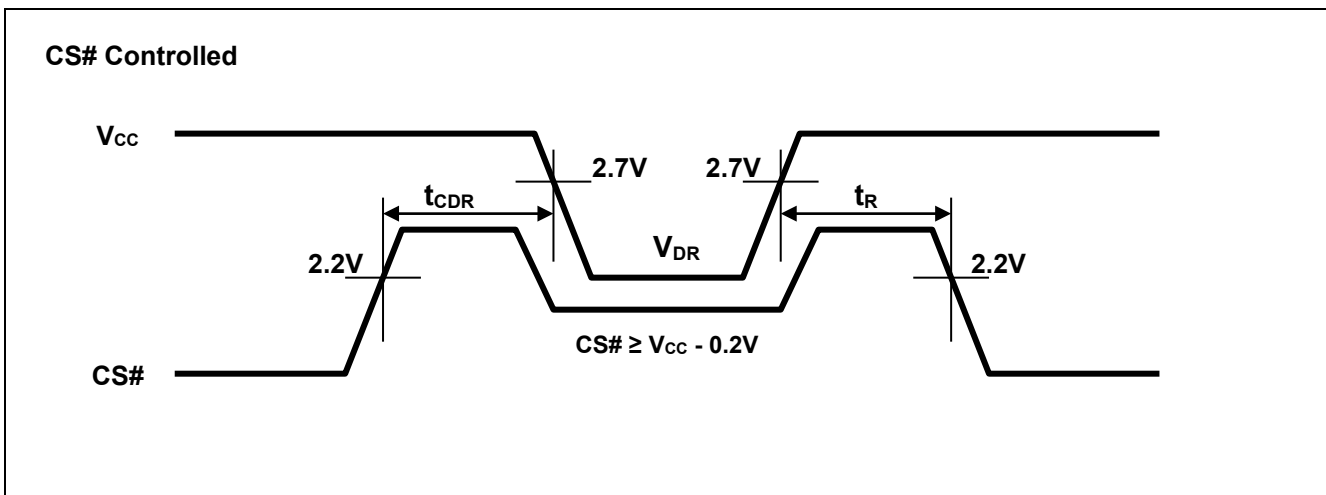
A write ends when any of CS# or WE# becomes inactive.

Low V_{CC} Data Retention Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions*25	
V _{CC} for data retention	V _{DR}	1.5	—	—	V	Vin ≥ 0V, CS# ≥ V _{CC} -0.2V	
Data retention current	I _{CCDR}	—	0.3*24	2	μA	~+25°C	V _{CC} =3.0V, Vin ≥ 0V, CS# ≥ V _{CC} -0.2V
		—	—	3	μA	~+40°C	
		—	—	5	μA	~+70°C	
		—	—	7	μA	~+85°C	
Chip deselect time to data retention	t _{CDR}	0	—	—	ns	See retention waveform.	
Operation recovery time	t _R	5	—	—	ms		

Note 24. Typical parameter indicates the value for the center of distribution at 3.0V ($T_a=25^\circ C$), and not 100% tested.

25. $CS\#$ controls address buffer, $WE\#$ buffer, $OE\#$ buffer, and I/O buffer. If $CS\#$ controls data retention mode, V_{in} levels (address, $WE\#$, $OE\#$, I/O) can be in the high-impedance state.

Low V_{CC} Data Retention Timing Waveforms ($CS\#$ controlled)

Revision History	RMLV0408E Series Data Sheet
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Rev.	Date	Description	
		Page	Summary
1.00	2014.2.27	—	First edition issued
2.00	2016.1.12	1	Changed section from “Part Name Information” to “Orderable part number information”
2.01	2020.2.20	Last page	Updated the Notice to the latest version
3.00	2021.8.18	1,4,10	Changed the typical value of I_{SB1} and I_{CCDR} from 0.4 μ A to 0.3 μ A. Revised orderable part number information

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